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a conductive layer over the substrate, the conductive layer being exposed to a material selected from the group consisting of phosphine and methylsilane to reduce an ability of the conductive layer to associate with oxygen.

Please add new claims 77-94 as follows:

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--77. (New) The in-process device of claim 75 wherein the other conductive layer comprises copper.

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78. (New) The in-process device of claim 73 further comprising a second conductive layer formed on the conductive layer and a third conductive layer formed on the second conductive layer.

79. (New) The in-process device of claim 78 wherein the conductive layer comprises a metal layer, the second conductive layer comprises a tungsten nitride layer, and the third conductive layer comprises copper.

80. (New) The in-process device of claim 73 wherein the substrate comprises a silicon substrate.

81. (New) An in-process device, comprising:
a substrate; and
a passivated conductive layer over the substrate, the passivated conductive layer having a reduced ability to associated with oxygen by being exposed to a material selected from the group consisting of phosphine and methylsilane.

82. (New) The in-process device of claim 81 wherein the conductive layer comprises tungsten nitride.

83. (New) The in-process device of claim 82 further comprising another conductive layer formed on the tungsten nitride layer.

84. (New) The in-process device of claim 83 wherein the other conductive layer comprises copper.

85. (New) The in-process device of claim 81 further comprising a second conductive layer formed on the conductive layer and a third conductive layer formed on the second conductive layer.

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86. (New) The in-process device of claim 85 wherein the conductive layer comprises a metal layer, the second conductive layer comprises a tungsten nitride layer, and the third conductive layer comprises copper.

87. (New) The in-process device of claim 81 wherein the substrate comprises a silicon substrate.

88. (New) An in-process device, comprising:
a substrate; and
a passivated conductive layer over the substrate, the passivated conductive layer having a reduced ability to associated with oxygen by being exposed to methylsilane.

89. (New) The in-process device of claim 88 wherein the conductive layer comprises tungsten nitride.

90. (New) The in-process device of claim 89 further comprising another conductive layer formed on the tungsten nitride layer.